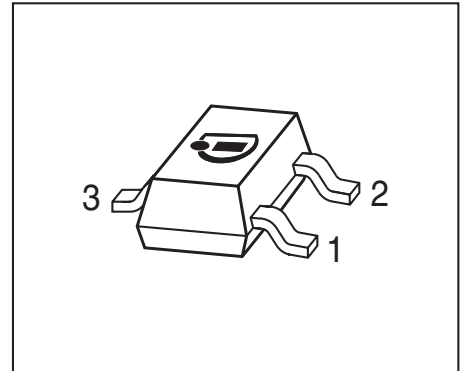


NPN Silicon High-Voltage Transistors

- Low collector-emitter saturation voltage
- Complementary types:
SMBTA92 / MMBTA92(PNP)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



Type	Marking	Pin Configuration			Package
SMBTA42/MMBTA42	s1D	1=B	2=E	3=C	SOT23

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	300	V
Collector-base voltage	V_{CBO}	300	
Emitter-base voltage	V_{EBO}	6	
Collector current	I_C	500	mA
Base current	I_B	100	
Total power dissipation- $T_S \leq 74 \text{ }^\circ\text{C}$	P_{tot}	360	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 210	K/W

¹For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

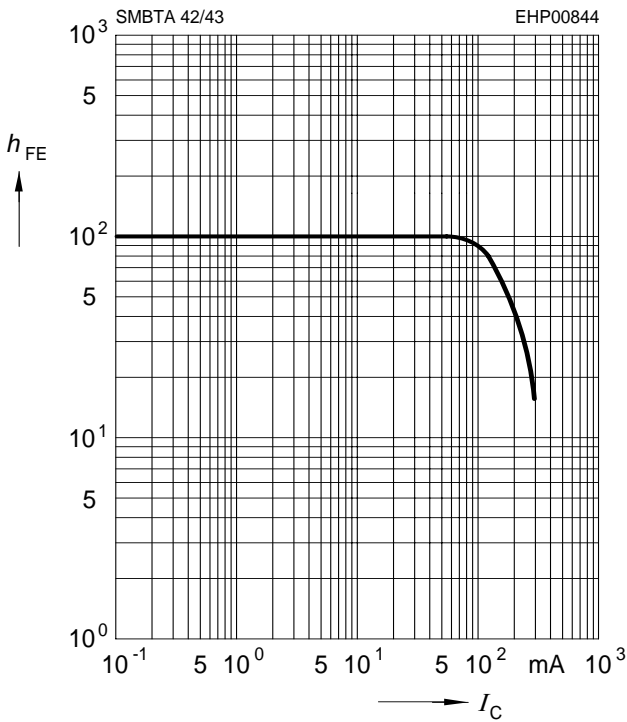
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	300	-	-	V
Collector-base breakdown voltage $I_C = 100\text{ }\mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	300	-	-	
Emitter-base breakdown voltage $I_E = 100\text{ }\mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	6	-	-	
Collector-base cutoff current $V_{CB} = 200\text{ V}, I_E = 0$ $V_{CB} = 200\text{ V}, I_E = 0, T_A = 150\text{ }^\circ\text{C}$	I_{CBO}	-	-	0.1 20	μA
Emitter-base cutoff current $V_{EB} = 5\text{ V}, I_C = 0$	I_{EBO}	-	-	100	nA
DC current gain ¹⁾ $I_C = 1\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 30\text{ mA}, V_{CE} = 10\text{ V}$	h_{FE}	25 40 40	- - -	- - -	-
Collector-emitter saturation voltage ¹⁾ $I_C = 20\text{ mA}, I_B = 2\text{ mA}$	V_{CEsat}	-	-	0.5	V
Base emitter saturation voltage ¹⁾ $I_C = 20\text{ mA}, I_B = 2\text{ mA}$	V_{BEsat}	-	-	0.9	
AC Characteristics					
Transition frequency $I_C = 10\text{ MHz}, V_{CE} = 20\text{ V}, f = 100\text{ MHz}$	f_T	50	70	-	MHz
Collector-base capacitance $V_{CB} = 20\text{ V}, f = 1\text{ MHz}$	C_{cb}	-	-	3	pF

¹⁾Pulse test: $t < 300\mu\text{s}$; $D < 2\%$

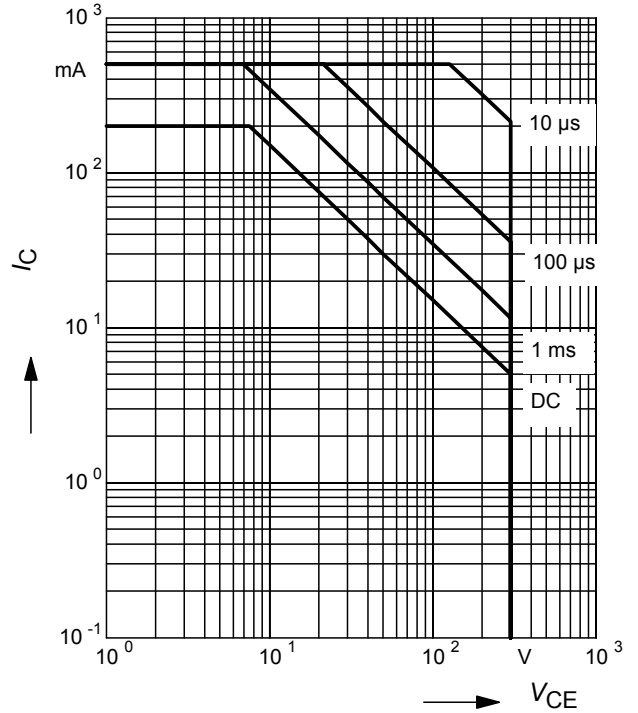
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 10\text{ V}$



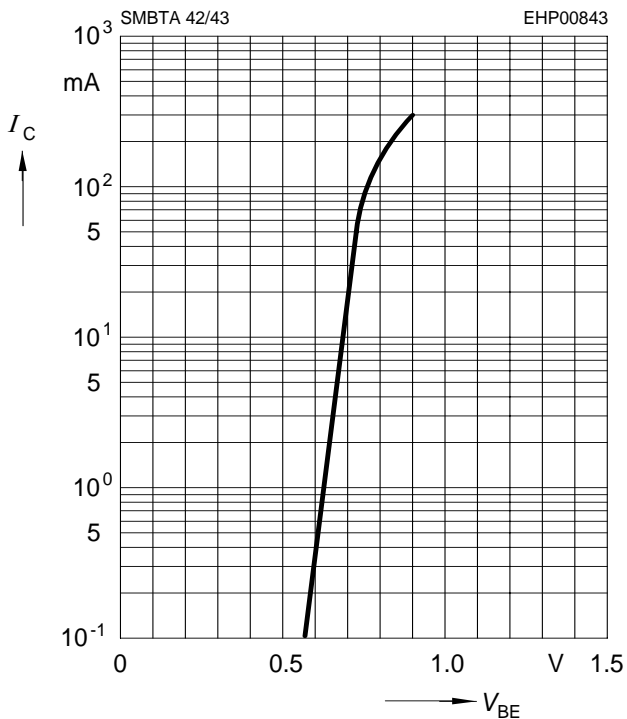
Operating range $I_C = f(V_{CE0})$

$T_A = 25^\circ\text{C}, D = 0$



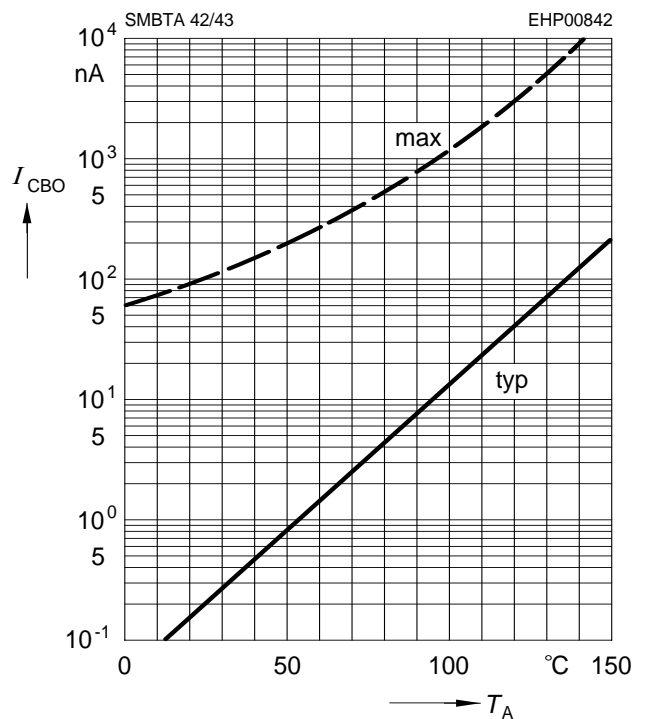
Collector current $I_C = f(V_{BE})$

$V_{CE} = 10\text{ V}$



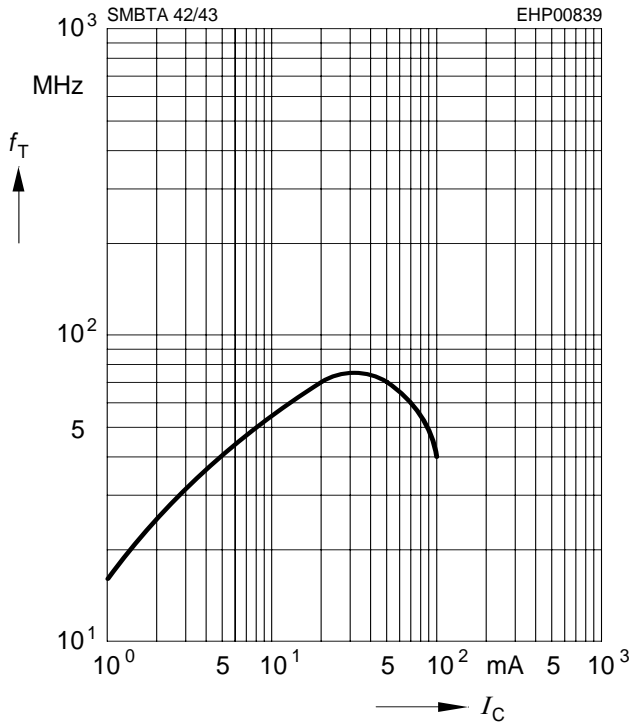
Collector cutoff current $I_{CBO} = f(T_A)$

$V_{CBO} = 160\text{ V}$



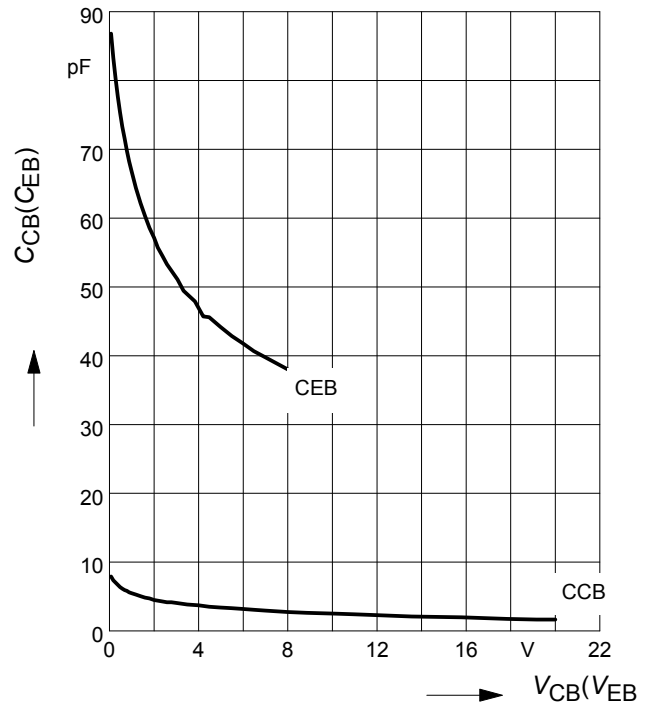
Transition frequency $f_T = f(I_C)$

$V_{CE} = 10\text{ V}, f = 100\text{ MHz}$



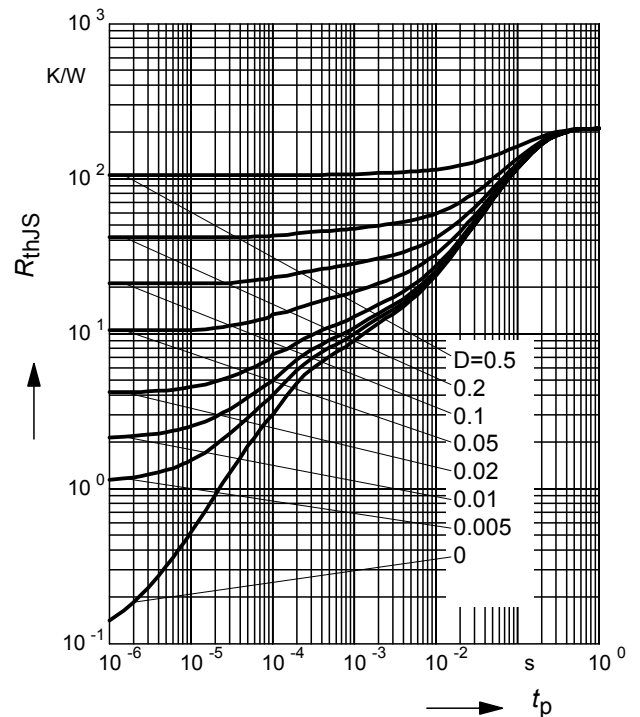
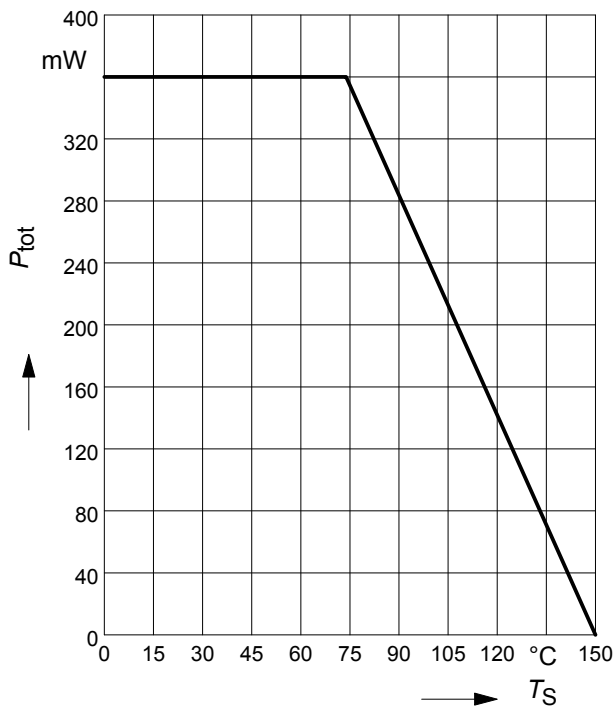
Collector-base capacitance $C_{cb} = f(V_{CB})$

Emitter-base capacitance $C_{eb} = f(V_{EB})$



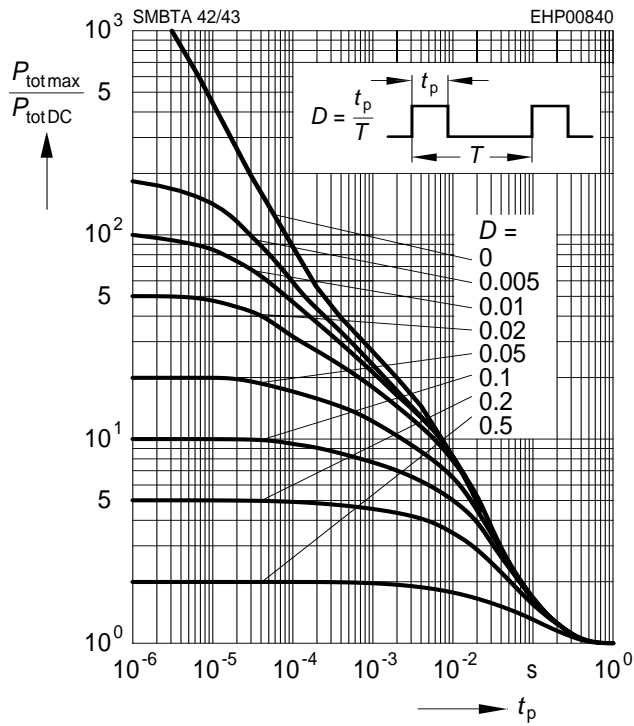
Total power dissipation $P_{tot} = f(T_S)$

Permissible Pulse Load $R_{thJS} = f(t_p)$



Permissible Pulse Load

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$



Package Outline



1) Lead width can be 0.6 max. in dambar area

Foot Print



Marking Layout (Example)



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel



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